/ Descriptions

VRW5606 Ł SQS ˥ Silicon PNP transistor in a SOT23-3 Plastic Package.

/ Features

Ⅵ ≍ ⊂ ∪Ḥ/ EU5VG4 : ; 5 P F T ´ ϒ AEC-Q101 ≍ ˎ ⌊

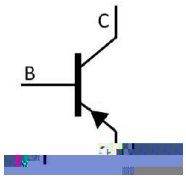
High breakdown, low $V_{CE(sat)}$,complements the BR2SD1782MCQ, Qualified to AEC-Q101 Standards for High Reliability, HF Product.

/ Applications

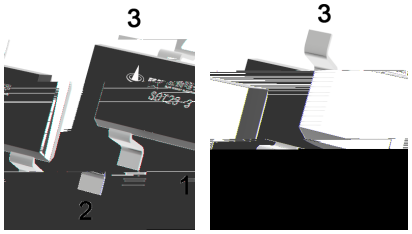
˜ ⅼ ’ ⊄ ⌊

Medium power amplifier applications, Meet the stringent requirements of automotive applications.

/ Equivalent Circuit



/ Pinning



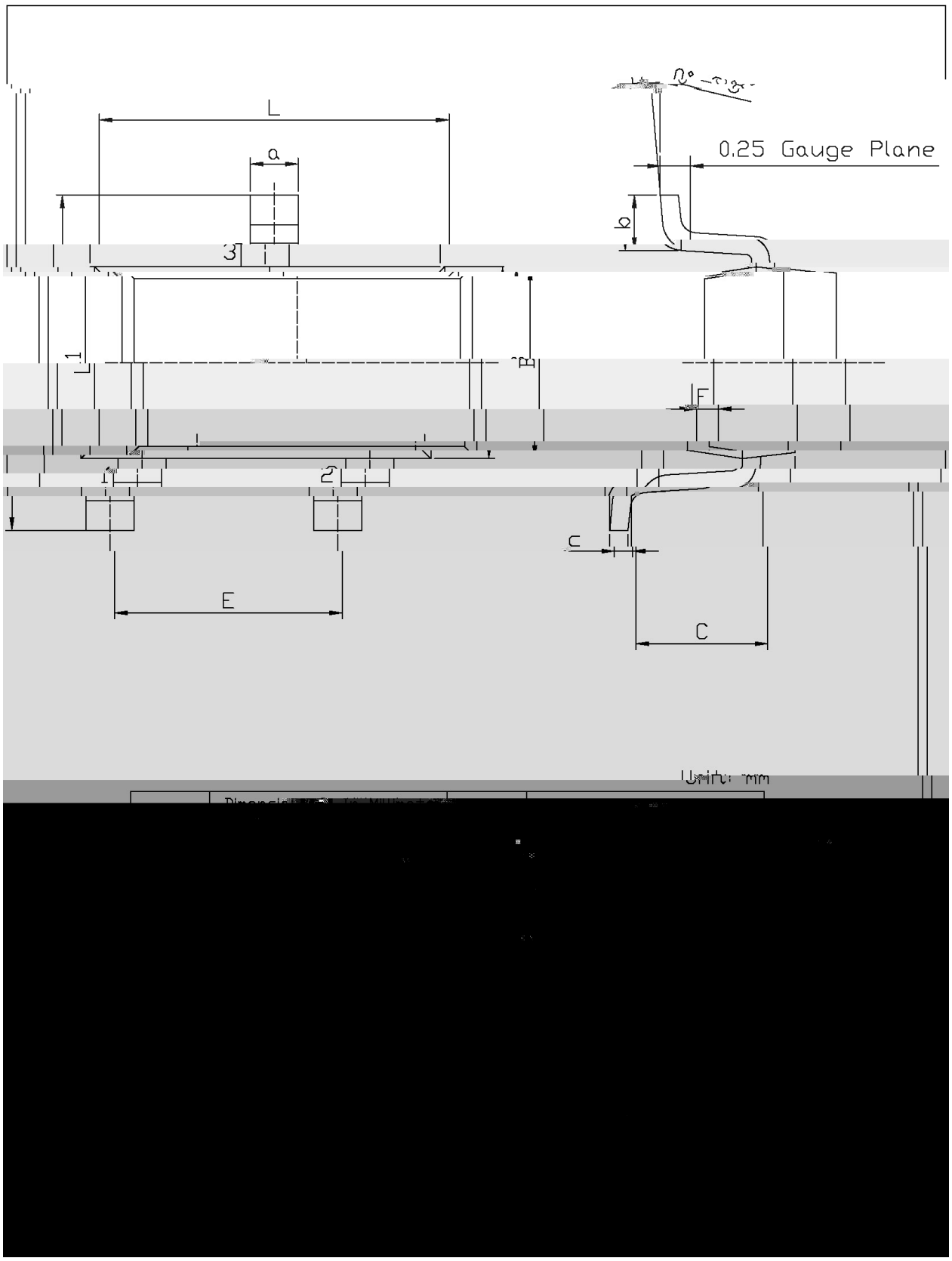
PIN1 Base PIN 2 Emitter PIN 3 Collector

/ h_{FE} Classifications & Marking

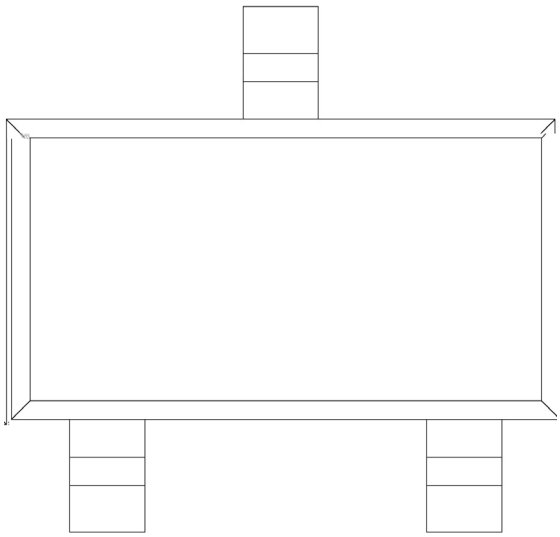
h_{FE} Classifications Symbol	Q	R
h_{FE} Range	120~270	180~390
Marking	QAKQ	QAKR

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-80	V
Collector to Emitter Voltage	V_{CEO}	-80	V
Emitter to Base Voltage	V_{EBO}	-5	V
Collector Current - Continuous	I_C	-500	mA

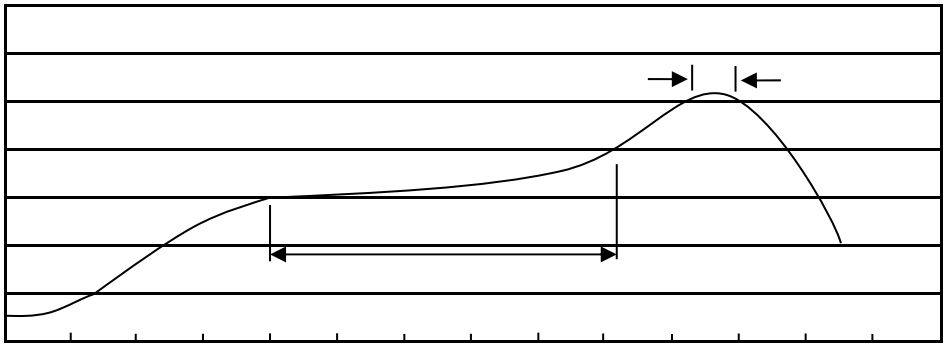
/ Package Dimensions



/ Marking Instructions



( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)



ب Note:

1 أ 150 200 ژ 60 120sec; 1.Preheating:150~200 , Time:60~120sec.

2 255±5 ژ ٨ 5±0.5sec; 2.Peak Temp.:255±5 , Duration:5±0.5sec.

3 ١ ھ 2 10 /sec. 3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

260±5 ژ 10±1 sec. Temp.:260±5 Time:10±1 sec

/ Packaging SPEC.

Ь / REEL

Package Type	Units					Dimension		(unit mm³)
	Units/Reel /	Reels/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Reel	Inner Box	Outer Box
SOT23-3	3,000	10	30,000	4	120,000	7 ×8	210×205×205	445×230×435

/ Notices